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TRANSMITTAL OF FORMAL DRAWINGS

Docket No. FIS920030410US1

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Khater, et al.

Serial No.	Filing Date	Confirmation No.	Examiner	Art Unit			
10/709,222	4/22/04						

Invention:

Structure and Method of Forming Bipolar Transistor Having a Self-Aligned Raised Extrinsic Base Using a Link-Up Region Formed from an Opening

Address to:

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Transmitted herewith are:

12 sheets of formal drawing(s) for this application.

Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

Daniel Schwerner Signance

H. Daniel Schnurmann

Agent

REGISTRATION NO.: 35,791

Dated:

July 20, 2004

I certify that this document and attached formal drawings are being deposited on July 20, 2004 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of Herson Mailing Correspondence

KAREN CINQ-MARS

Typed or Printed Name of Person Mailing Correspondence